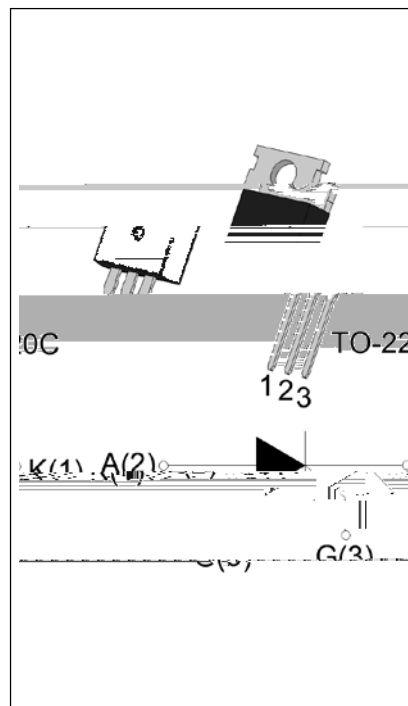




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1630C SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-220C is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	30	A
V_{DRM}/V_{RRM}	1600	V
I_{GT}	40	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	1600	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	1600	V
Average on-state current ($T_C=86^\circ C$)	$I_{T(AV)}$	19	A
RMS on-state current ($T_C=86^\circ C$)	$I_{T(RMS)}$	30	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	300	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		320	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	450	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	200	A/s
Peak gate current ($t_p=20\mu s, T_j=125^\circ C$)	I_{GM}	10	A

JCT1630C

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Average gate power dissipation ($T_j=125^{\circ}\text{C}$) $P_{avg} = \frac{1}{T} \int_0^T P_{sw} dt = \frac{Q E T_c}{T} = 0.2878 \text{ W}$

TEL

JCT1630C

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J CT 16 30 C

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FIG.7

PACKAGE MECHANICAL DATA



